RT1P137L

TRANSISTOR WITH RESISTOR FOR SWITCHING APPLICATION SILICON PNP EPITAXIAL TYPE

DESCRIPTION

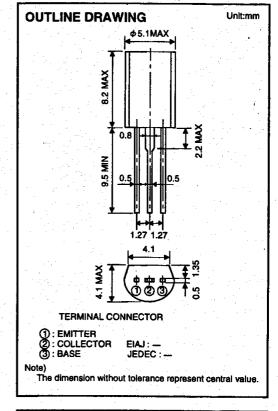
RT1P137L is a one chip transistor with built-in bias resistor, NPN type is RT1N137L.

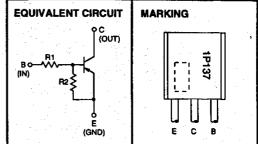
FEATURE

- Built-in bias resistor (R1=1kΩ,R2=22kΩ)
- ●High collector current Ic=-1A
- ●Low VCE(sat) VCE(sat)=-0.3Vmax (@IC=-300mA,IB=-3mA)
- ●High collector dissipation Pc=900mW

APPLICATION

Inverted circuit, switching circuit, interface circuit, driver circuit.





MAXIMUM RATINGS (Ta=25°C)

Symbol	Parameter	Ratings	Unit	
Vсво	Collector to Base voltage	-40	V	
VEBO	Emitter to Base voltage	-6	. V	
VCEO	Collector to Ernitter voltage	-40	V	
lc	Collector current	-1	A	
Ісм	Peak Collector current	-2	Α	
Pc	Collector dissipation(Ta=25°C)	900	mW	
Tj	Junction temperature	+150	°C	
Tstg	Storage temperature	-55 to +150	ర	

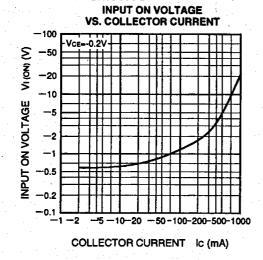
ELECTRICAL CHARACTERISTICS (Ta=25°C)

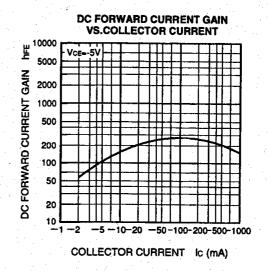
Symbol	Parameter	Test conditions		Limits		
		Test colluitions	Min	Тур	Max	Unit
V(BR)CEO	C to E break down voltage	Ic=-1mA,RBE=∞	-40			٧
Ісво	Collector cut off current	VCB=-40V,IE=0			-0.1	μА
hre	DC forward current gain	VcE=-5V,Ic=-100mA	100			
VCE(sat)	C to E saturation voltage	Ic=-300mA,Is=-3mA	,	-0.1	-0.3	V
VI(ON)	Input on voltage	VcE=-0.2V,lc=-300mA		-2.4	-4.0	V
VI(OFF)	Input off voltage	VCE=-5V,IC=-100 μ A	0.4	0.53		V
Rı	Input resistor		0.7	1.0	1.3	kΩ
R2/R1	Resistor ratio		20	22	24	_
fr	Gain band width product	VcE=-6V,IE=10mA		130		MHz

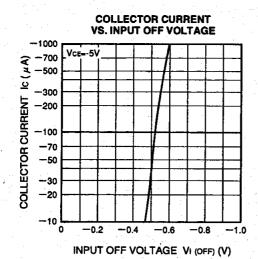
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TRANSISTOR WITH RESISTOR FOR SWITCHING APPLICATION SILICON PNP EPITAXIAL TYPE

TYPICAL CHARACTERISTICS









http://www.idc-com.co.jp 6-41, TSUKUBA, ISAHAYA, NAGASAKI, 854-0065, JAPAN

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